

EUROPEAN PATENT OFFICE

Patent Abstracts of Japan

PUBLICATION NUMBER : 63055978
PUBLICATION DATE : 10-03-88

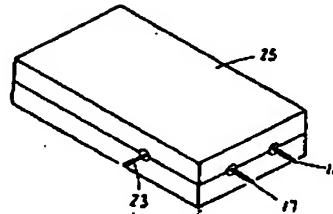
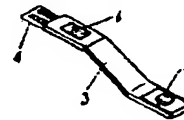
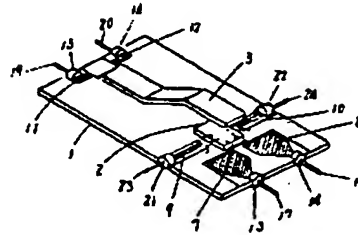
APPLICATION DATE : 26-08-86
APPLICATION NUMBER : 61199361

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INT.CL. : H01L 29/80 H01L 25/16 H01L 31/12

TITLE : SEMICONDUCTOR DEVICE



ABSTRACT : PURPOSE: To improve the performance of a semiconductor device, by accommodating a light emitting element, which emits light to the surfaces of a GaAs- MESFET and a GaAs-MESFET in a common package, thereby implementing the high speed performance of a single gate FET and the characteristics adjusting functions of a dual-gate FET.

CONSTITUTION: On the surface of a ceramic substrate 1 of a semiconductor device, a GaAs-MESFET chip 2 and a light-emitting-element attaching member 3 are fixed. The member 3 is formed by bending a metal plate in a crank shape. A light emitting power source is supplied to a light emitting element 5, which is attached to the member 3, from a flexible printed wiring board 4. A bonding member 6 by which the member 3 is fixed to the substrate 1 is provided at the other end of the member 3 with respect to the element 5. The member 3 is turned over so that the element 5 faces the surface of the chip 2. The member 3 is fixed to the substrate 1 through the member 6. Thus, the high speed performance of a single gate GaAs-MESFET and the characteristic adjusting functions of a dual-gate GaAs-MESFET are implemented.

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